
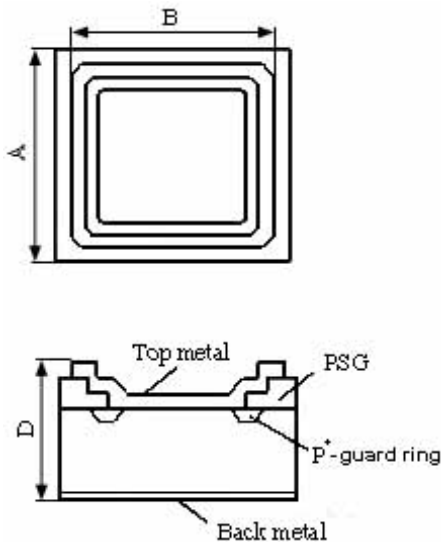


		2A/125V. Die Size-51mil.		
				
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	125	130
Average Rectified Forward Current	$I_{F(AV)}$	A	2,0	-
DC Forward Voltage @ 25°C, $I_F=2,0\text{A}$	$V_F$	V	0,83	0,81
Maximum Reverse Current @ 25°C, $V_R=125\text{V}$ @ 125°C, $V_R=125\text{V}$	$I_R$	mA	0,005 6,0	0,003 4,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	60	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<175^\circ\text{C}$ .	$I_{RRM}$	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	$V_{ESD}$	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	175	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	1300
$B_x$ $B_y$	Top Metal Size	1160
D	Thickness	300max.
Scribe line Width		80

*Top metal:*  
 a) **Al-Ni-Ag** – for Soldering;  
 b) **Al** – for Wire Bonding.  
 Backside metal: **Ti-Ni-Ag**.